L Number	Hits	Search Text	DB	Time stamp
1	2496	257/751.ccls. 257/752.ccls. 257/759.ccls. 257/760.ccls. 257/762.ccls.	USPAT; US-PGPUB	2004/05/25 09:48
2	414	(msq (methyl adj silsesquioxane)) and ((barrier with (dielectric insulator carbide nitride oxide oxynitride)) electromigration diffusion)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/25 09:59
4	231	((polymeric adj alkyl adj siloxane) sicoh sioch (polymeric adj silicon adj carbide) "sic(h)") and ((barrier with (dielectric insulator carbide nitride oxide oxynitride)) electromigration diffusion)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/25 10:55
5	64	((polymeric adj alkyl adj siloxane) sioch sicoh) and ((polymeric adj silicon adj carbide) "sic(h)")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/25 11:16
6	33	(257/751.ccls. 257/752.ccls. 257/759.ccls. 257/760.ccls. 257/762.ccls.) and ((polymeric adj alkyl adj siloxane) sicoh sioch (polymeric adj silicon adj carbide) "sic(h)")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/25 11:21
7	234	(257/$.ccls. 438/$.ccls.) and ((polymeric adj alkyl adj siloxane) sicoh sioch sich (polymeric adj silicon adj carbide) "sic(h)")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/25 11:25
8	45	MIKAGI-K MIKAGI-KAORU	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/25 11:47
9	45	(257/751.ccls. 257/752.ccls. 257/759.ccls. 257/760.ccls. 257/762.ccls.) and ((silicon wafer semiconductor) and (damascene inlaid "in-laid") and ((copper cu) same seed same (electroplat$3 plat43) same (cmp planar$8)))	USPAT; US-PGPUB	2004/05/25 11:51
10	47	(257/751.ccls. 257/752.ccls. 257/759.ccls. 257/760.ccls. 257/762.ccls.) and (((dielectric insulat$4 oxide dioxide sioch sicoh sich "low-k" "low k") near4 barrier) with (reduc$5 redox deoxid$7))	USPAT; US-PGPUB	2004/05/25 12:02

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